

IN THE CLAIMS

Please amend the claims as follows.

For the Examiner's convenience, a list of all claims is included below.

1-28 (Canceled)

29. (Currently amended) A wafer processing apparatus, comprising:

a processing chamber defined by a lower wall, an upper wall and side walls extending from the lower wall to the upper wall, a wafer supply opening being formed in one of the walls for transferring a wafer into the chamber;

a susceptor in the chamber on which the wafer can be located so that an upper surface of the wafer faces the upper wall;

a manifold component located on the chamber and, together with the upper surface of the upper wall, defining a manifold cavity;

an exhaust line connected to the chamber, for flowing a gas from the chamber, connected such that the gas has a tendency to flow toward the exhaust line; and

a gas supply line connected to the manifold component, the gas supply connected via a gas supply line opening formed through an upper surface of the manifold cavity, wherein the upper wall has a plurality of gas supply openings, each of the gas supply openings formed into an upper surface and out of a lower surface of the upper wall such that each gas supply opening is defined by a corresponding interior surface of the upper wall, the gas supply openings being nonuniformly distributed over the upper wall to create a flow pattern that counteracts the tendency of the gas to flow toward the exhaust line, and thus promotes even processing over the

upper surface of the wafer.

30. (Previously presented) The apparatus of claim 29 wherein the openings are more densely located on one side of the upper wall than on another side thereof.
31. (Previously presented) The apparatus of claim 30 wherein the openings are substantially equal in size.
32. (Previously presented) The apparatus of claim 29 wherein flow of gas in the chamber is laminar.
33. (Previously presented) The apparatus of claim 29 wherein the exhaust line is connected at an exhaust location which is off-center with respect to a center point of the wafer, when viewed from above, so that the gas exits out of the chamber at the exhaust location which is off-center with respect to a center point of the wafer.
34. (Previously presented) The apparatus of claim 33 wherein a channel is defined within the chamber, the channel being concentric with the wafer, gas flowing radially outwardly over the wafer into the channel, from the channel, to the exhaust location into the exhaust line.
35. (Previously presented) The apparatus of claim 34 wherein the openings are more densely located farther from the exhaust location.

36-37 (Canceled)

38. (Previously Presented) The apparatus of claim 29 wherein there are first and second ones of the openings on opposing sides of a point on the upper wall, the first opening having a lower end which is angularly displaced relative to an upper end thereof in a selected direction about the point, and the second opening having a lower end which is angularly displaced relative to an upper end thereof in the selected direction, so that the openings jointly create a circular gas flow pattern in the chamber.

39. (Previously Presented) The apparatus of claim 38 wherein a third of the openings, on a side of the second opening opposing the first opening, has a lower end which is displaced in the first direction relative to an upper end thereof.

40. (Previously Presented) The apparatus of claim 29 wherein the exhaust line is connected at an exhaust location which is off-center with respect to a center point of the wafer, when viewed from above, so that the gas exits out of the wafer at the exhaust location which is off-center with respect to a center point of the wafer.

41. (Previously Presented) The apparatus of claim 40 wherein the openings are formed to increase a flowrate of the gas over the wafer farther from the exhaust location.